Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended): A high electron mobility transistor using a Group III-V compound semiconductor, comprising:

an undoped second channel layer laminated on an InP substrate via a buffer layer;

an undoped first channel layer laminated on said second channel layer; and

a doped electron-supplying layer laminated ~~on~~ in contact with said first channel layer,

wherein said first channel layer is composed of $In_{1-x}Ga_xAs$ and has an energy level of conduction band lower than that of said electron-supplying layer,

said second channel layer is composed of a Group III-V compound semiconductor using a Group V element other than P, has an energy level of conduction band higher than that of the first channel layer, has a band gap wider than that of the first channel layer, and has a thickness larger than that of the first channel layer.

2. (Original): The high electron mobility transistor as described in claim 1, wherein said first and second channel layers are formed to have a thickness small enough to have discrete quantum levels, a first quantum level being formed only in the first

channel layer, and a second quantum level being formed in both the first and second channel layers.

3. (Previously Amended): The high electron mobility transistor as described in claim 1, wherein said electron-supplying layer is composed of $In_{1-y}Al_yAs$, the first channel layer is composed of $In_{1-x}Ga_xAs$, and the second channel layer is composed of $In_{1-x}(Al_{1-z}Ga_z)_xAs$.

4. (Withdrawn): The high electron mobility transistor as described in claim 1 or claim 2, wherein said electron-supplying layer is composed of $In_{1-y}Al_yAs$, the first channel layer is composed of $In_{1-x}Ga_xAs$, and the second channel layer is composed of $In_{1-x}(Al_{1-z}Ga_z)_x(As_{1-z2}Sb_{z2})$.

5. (Previously Amended): The high electron mobility transistor as described in claim 3, wherein the thickness of said first channel layer is 3~7 nm.

6. (Previously amended): The high electron mobility transistor as described in claim 3, wherein the thickness of said second channel layer is 10~20 nm.

7. (Previously amended): The high electron mobility transistor as described in claim 3, wherein the composition ratio (1-z) of Al element in said second channel layer is 0.05~0.5.

8. (Previously Amended): The high electron mobility transistor as described in claim 1, wherein said electron-supplying layer is composed of $In_{1-y}Al_yAs$, the first channel layer is composed of $In_{1-x}Ga_xAs$, and the second channel layer is composed of $In_{1-x}Ga_xAs$ with the In composition ratio lower and the gallium composition ratio higher than those in the first channel layer.

9. (Previously Amended): The high electron mobility transistor as described in claim 1, wherein an element separation groove is formed which extends from said electron-supplying layer to said buffer layer.

10. (Currently Amended): A high electron mobility transistor using a Group III-V compound semiconductor, comprising :

an undoped second channel layer laminated on an InP substrate via a buffer layer and composed of $In_{1-x}(Al_{1-z}Ga_z)_xAs$ (where the composition ratio (z-1) of Al is 0.05~0.5) which is lattice matched to InP,

an undoped first channel layer laminated on said second channel layer and composed of $In_{1-x}Ga_xAs$ which is lattice matched to InP, and

a doped electron-supplying layer laminated ~~on~~ in contact with said first channel layer and composed of $In_{1-y}Al_yAs$ which is lattice matched to InP.

11. (Original): The high electron mobility transistor as described in claim 10, wherein said first and second channel layers are formed to have a thickness small enough to have the discrete quantum levels, a first quantum level being formed only in the first

channel layer, and a second quantum level being formed in both the first and second channel layers.

12. (Currently Amended): A high electron mobility transistor using a Group III-V compound semiconductor, comprising

an undoped second channel layer laminated on an InP substrate via a buffer layer;

an undoped first channel layer laminated on said second channel layer; and

a doped electron-supplying layer laminated ~~on~~ in contact with said first channel layer,

wherein said first channel layer is composed of $In_{1-x}Ga_xAs$ and has an energy level of conduction band lower than that of said electron-supplying layer,

said second channel layer is composed of a Group III-V compound semiconductor using a Group V element other than P, has an energy level of conduction band higher than that of the first channel layer, and has a band gap wider than that of the first channel layer,

wherein said electron-supplying layer is composed of $In_{1-y}Al_yAs$, the first channel layer is composed of $In_{1-x}Ga_xAs$, and the second channel layer is composed of $In_{1-x}(Al_{1-z}Ga_z)_xAs$,

wherein the composition ratio (1-z) of Al element in said second channel layer is 0.05~0.5.

13. (Withdrawn): The high electron mobility transistor as described in claim 4, wherein the thickness of said first channel layer is 3~7 nm.

14. (Withdrawn): The high electron mobility transistor as described in claim 4, wherein the thickness of said second channel layer is 10~20 nm.

15. (Withdrawn): The high electron mobility transistor as described in claim 4, wherein the composition ratio (1~z) of Al element in said second channel layer is 0.05~0.5.

16. (Previously Added): The high electron mobility transistor as described in claim 2, wherein said electron-supplying layer is composed of $In_{1-y}Al_yAs$, the first channel layer is composed of $In_{1-x}Ga_xAs$, and the second channel layer is composed of $In_{1-x}Ga_xAs$ with the In composition ratio lower and the gallium composition ratio higher than those in the first channel layer.

17. (Previously Added): The high electron mobility transistor as described in claim 2, wherein an element separation groove is formed which extends from said electron-supplying layer to said buffer layer.

18. (Previously Added): The high electron mobility transistor as described in claim 2, wherein said electron-supplying layer is composed of $In_{1-y}Al_yAs$, the first

channel layer is composed of $In_{1-x}Ga_xAs$, and the second channel layer is composed of $In_{1-x}(Al_{1-z}Ga_z)_xAs$.

19. Deleted

20. Deleted

21. (Currently Amended): A high electron mobility transistor using a Group III-V compound semiconductor, comprising:

an undoped second channel layer laminated on an InP substrate via a buffer layer;

an undoped first channel layer laminated on said second channel layer; and

a doped electron-supplying layer laminated ~~on~~ in contact with said first channel layer,

wherein said first channel layer is composed of $In_{1-x}Ga_xAs$ and has an energy level of conduction band lower than that of said electron-supplying layer,

said second channel layer is composed of a Group III-V compound semiconductor using a Group V element other than P, has an energy level of conduction band higher than that of the first channel layer, has a band gap wider than that of the first channel layer, and has a thickness larger than that of the first channel layer

wherein the doped electron-supplying layer, the undoped first channel layer and the undoped second channel layer are the group III-V compound semiconductor being lattice-matched to the InP substrate.